

SOT-363 Plastic-Encapsulate Transistors

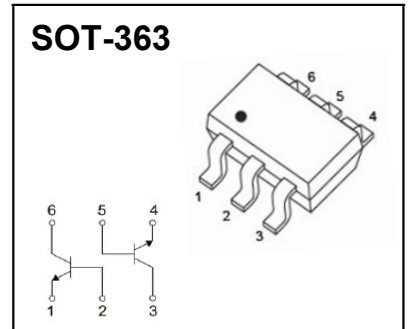
MMDT3904 DUAL TRANSISTOR (NPN+NPN)

FEATURES

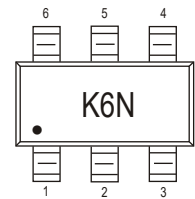
- Epitaxial planar die construction
- Ideal for low power amplification and switching
- High Stability and High Reliability

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	60	V
V_{CE0}	Collector-Emitter Voltage	40	V
V_{EB0}	Emitter-Base Voltage	5	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$



MARKING: K6N

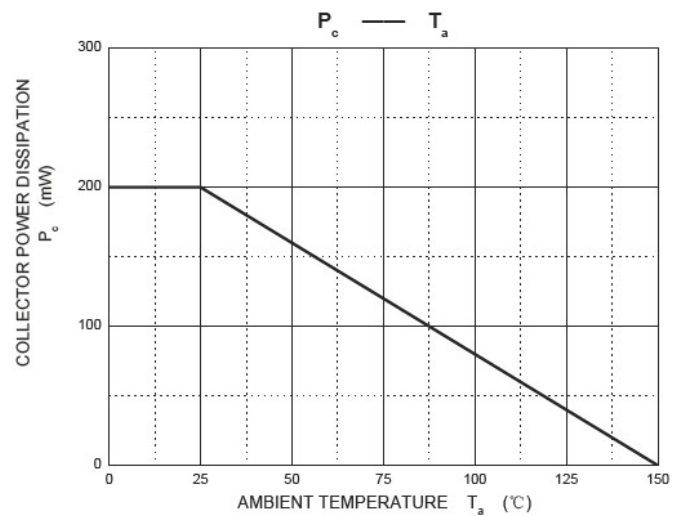
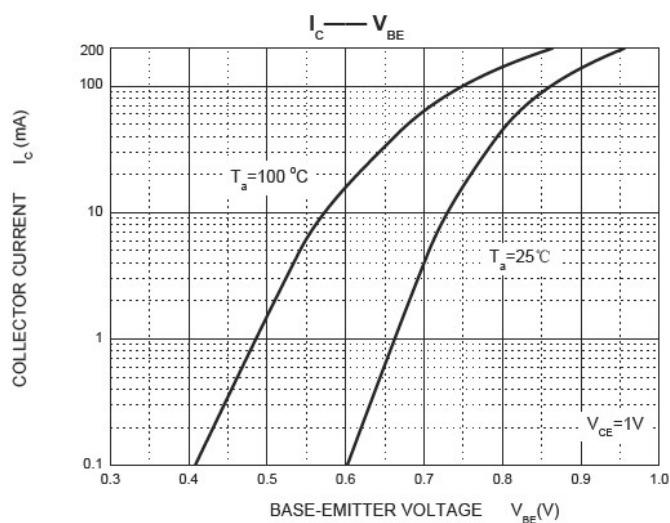
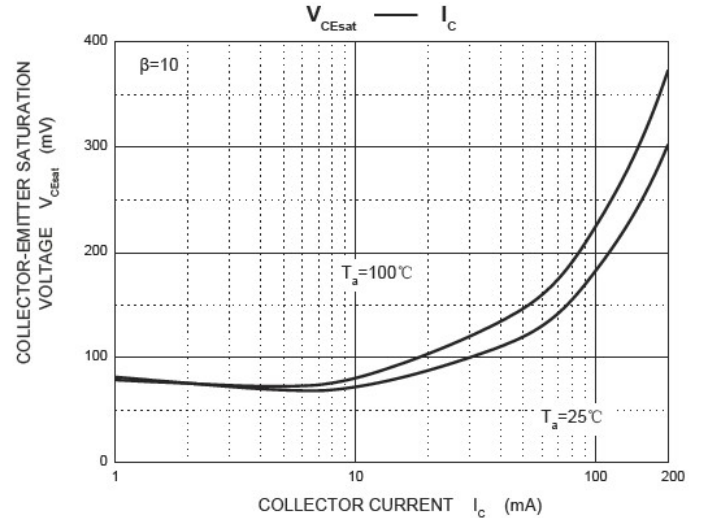
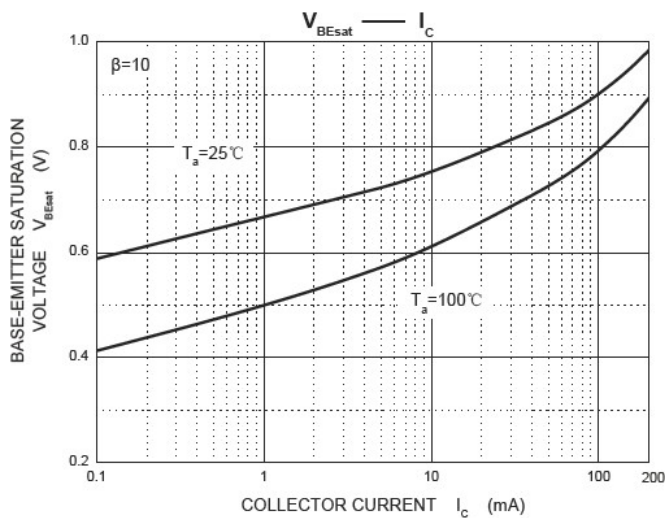
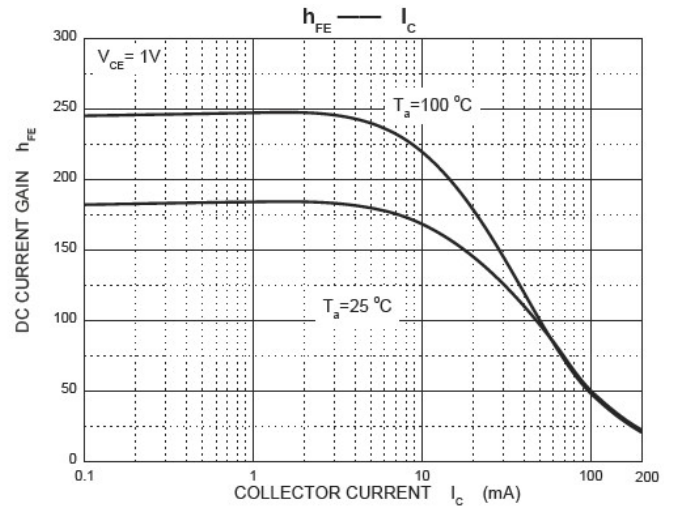
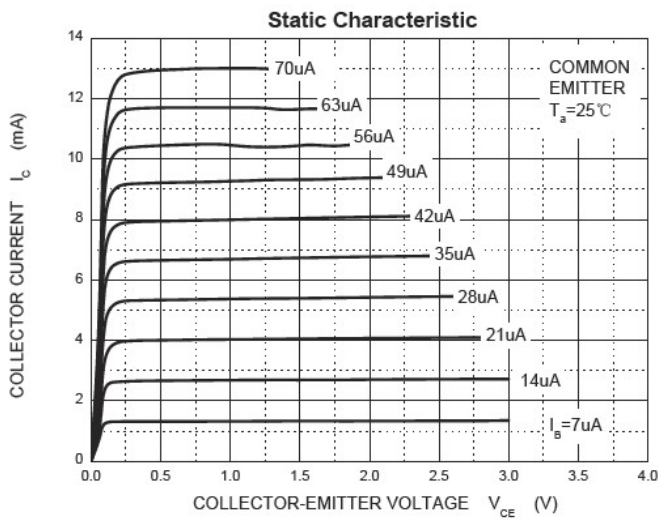


ELECTRICAL CHARACTERISTICS ($T_a= 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}$, $I_C=0$	5			V
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}$, $V_{EB(off)}=3\text{V}$			50	nA
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}$, $I_E=0$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			50	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}$, $I_C=0.1\text{mA}$	40			
	$h_{FE(2)}$	$V_{CE}=1\text{V}$, $I_C=1\text{mA}$	70			
	$h_{FE(3)}$	$V_{CE}=1\text{V}$, $I_C=10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=1\text{V}$, $I_C=50\text{mA}$	60			
	$h_{FE(5)}$	$V_{CE}=1\text{V}$, $I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}$, $I_B=1\text{mA}$			0.2	V
		$I_C=50\text{mA}$, $I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}$, $I_B=1\text{mA}$	0.65		0.85	V
		$I_C=50\text{mA}$, $I_B=5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	300			MHz
Collector output capacitance	C_{ob}	$V_{CB}=5\text{V}$, $I_E=0$, $f=1\text{MHz}$			4	pF
Noise figure	NF	$V_{CE}=5\text{V}$, $I_C=0.1\text{mA}$, $f=1\text{KHz}$, $R_s=1\text{K}\Omega$			5	dB
Delay time	t_d	$V_{CC}=3\text{V}$, $V_{BE(off)}=-0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1\text{mA}$			35	ns
Rise time	t_r	$V_{CC}=3\text{V}$, $V_{BE(off)}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1\text{mA}$			35	ns
Storage time	t_s	$V_{CC}=3\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1\text{mA}$			200	ns
Fall time	t_f	$V_{CC}=3\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1\text{mA}$			50	ns

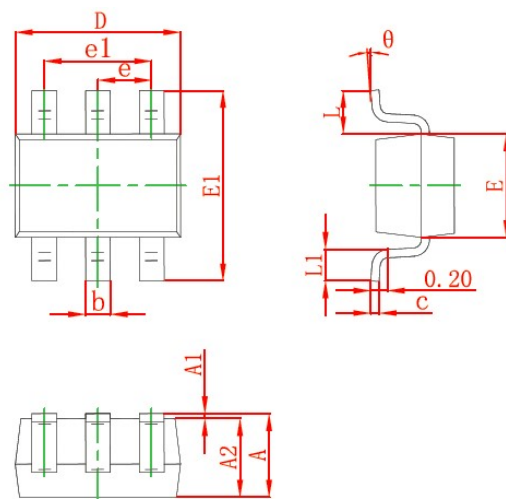
Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$

Typical Characteristics



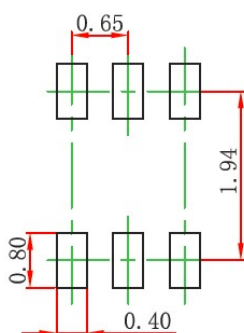
Outlitne Drawing

SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.100	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.400
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°

Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.